SK 60 GAL 123

SEMITOP® 2

IGBT Module

SK 60 GAR 123

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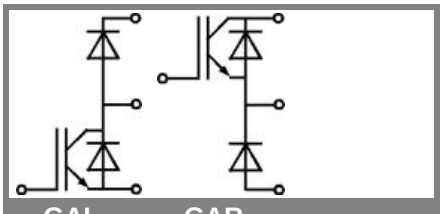
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding aluminium oxide ceramic (DBC)
- High short circuit capability
- NPT (Non-Punch-Through technology)
- $V_{ce(sat)}$ with positive coefficient
- Low tail with low temperature dependance

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GAL GAR

Absolute Maximum Ratings	T_s = 25 °C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
V_{GES}		± 20	V
I_C	T_s = 25 (80) °C;	58 (40)	A
I_{CM}	t_p < 1 ms; T_s = 25 (80) °C;	116 (80)	A
T_j		- 40 ... + 150	°C
Freewheeling CAL diode			
I_F	T_s = 25 (80) °C;	57 (38)	A
I_{FM} = - I_{CM}	t_p < 1 ms; T_s = 25 (80) °C;	104 (38)	A
T_j		- 40 ... + 150	°C
T_{stg}		- 40 ... + 125	°C
T_{sol}	Terminals, 10 s	260	°C
V_{isol}	AC 50 Hz, r.m.s. 1 min. / 1 s	2500 / 3000	V

Characteristics	T_s = 25 °C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{CE(sat)}$	I_C = 50 A, T_j = 25 (125) °C		2,5 (3,1)	3 (3,7)	V
$V_{GE(th)}$	V_{CE} = V_{GE}; I_C = 0,002 A	4,5	5,5	6,5	V
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V; 1 MHz		3,3		nF
$R_{th(j-s)}$	per IGBT			0,6	K/W
	per module				K/W
	under following conditions:				
$t_{d(on)}$	V_{CC} = 600 V , V_{GE} = ± 15 V		70		ns
t_r	I_C = 50 A, T_j = 125 °C		90		ns
$t_{d(off)}$	R_{Gon} = R_{Goff} = 22 Ω		460		ns
t_f			30		ns
E_{on} + E_{off}	Inductive load		16		mJ
Freewheeling CAL diode					
V_F = V_{EC}	I_F = 50 A; T_j = 25 (125) °C		2 (1,8)	2,5	V
$V_{(TO)}$	T_j = (125) °C		(1)	(1,2)	V
r_T	T_j = (125) °C		(18)	(22)	mΩ
$R_{th(j-s)}$				0,9	K/W
	under following conditions:				
I_{RRM}	I_F = 50 A; V_R = 600 V		40		A
Q_{rr}	dI_F/dt = -800 A/µs		8		µC
E_{off}	V_{GE} = 0 V; T_j = 125 °C		2,3		mJ
Mechanical data					
M1	mounting torque			2	Nm
w			19		g
Case	SEMITOP® 2		T 18		

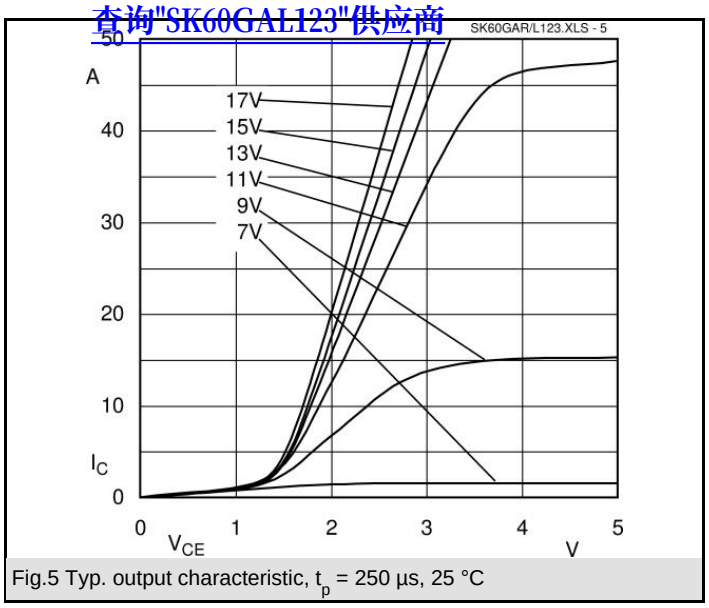


Fig.5 Typ. output characteristic, t_p = 250 µs, 25 °C

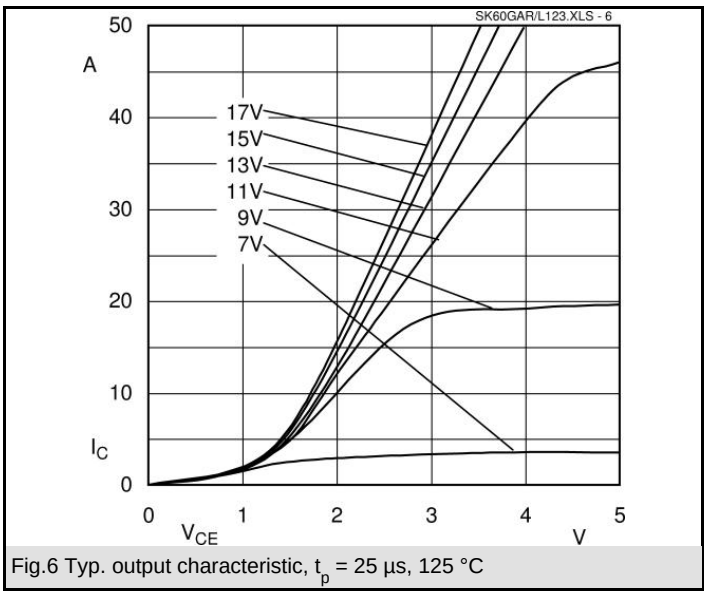


Fig.6 Typ. output characteristic, t_p = 25 µs, 125 °C

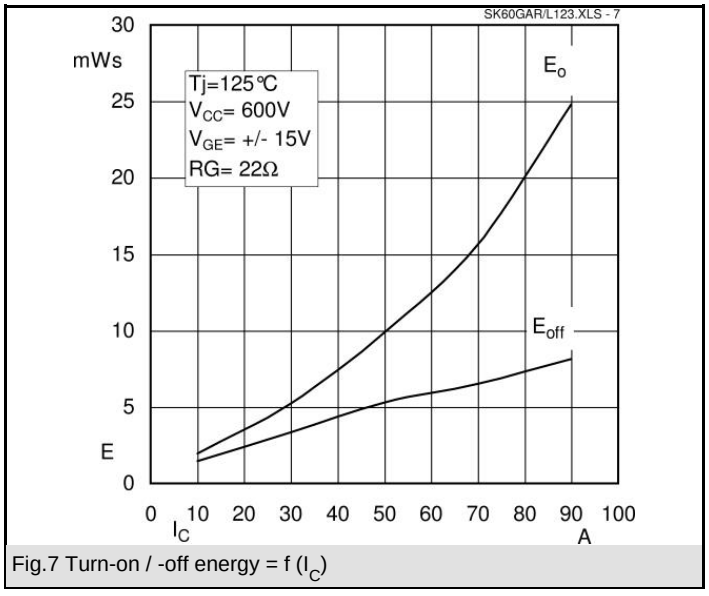


Fig.7 Turn-on / -off energy = f (I_C)

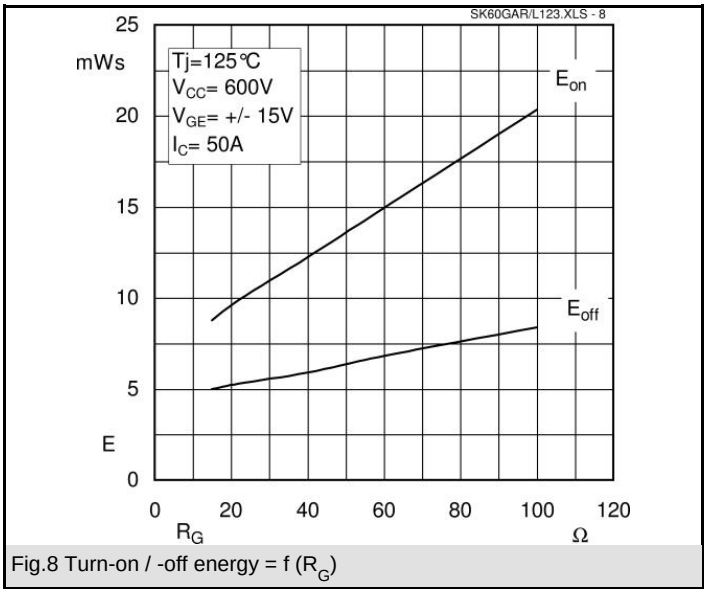


Fig.8 Turn-on / -off energy = f (R_G)

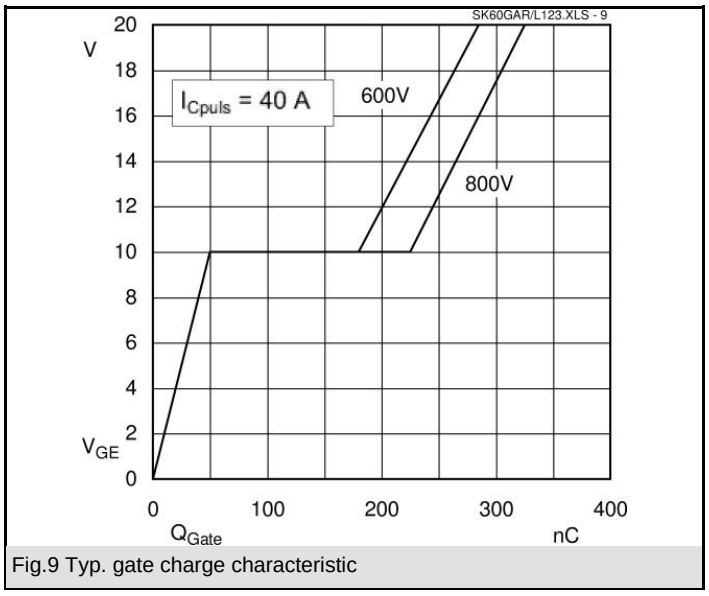


Fig.9 Typ. gate charge characteristic

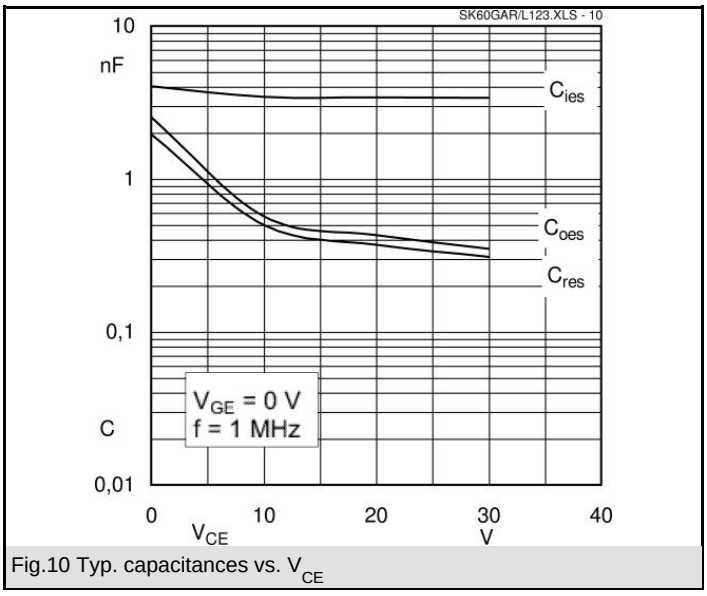


Fig.10 Typ. capacitances vs. V_{CE}

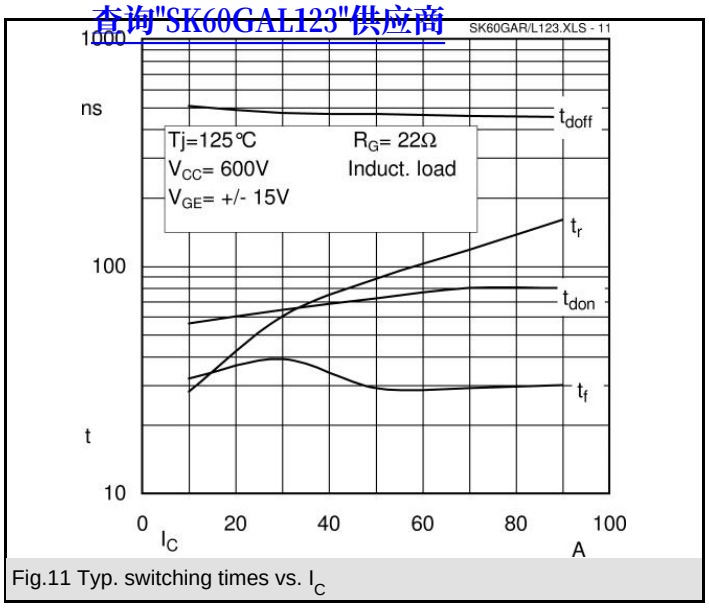


Fig.11 Typ. switching times vs. I_C

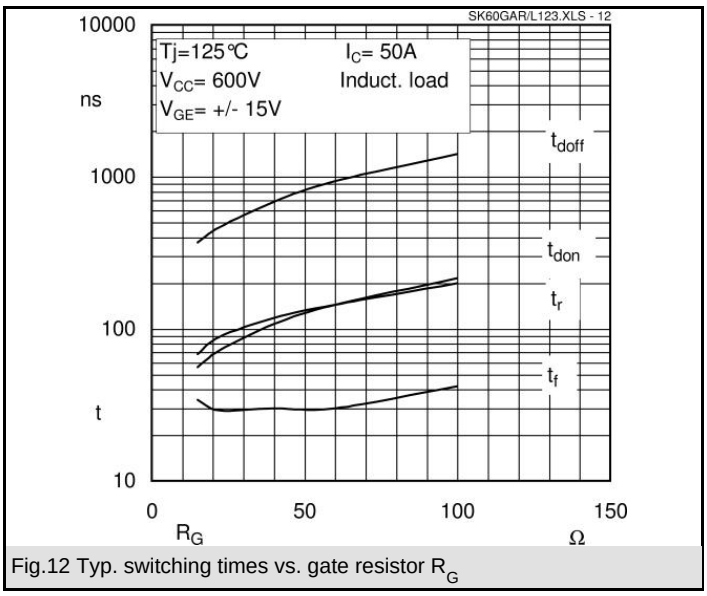


Fig.12 Typ. switching times vs. gate resistor R_G

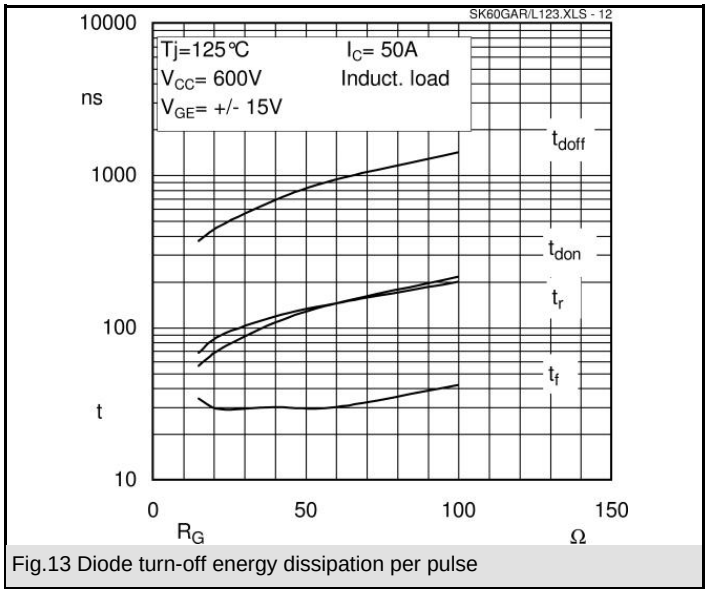


Fig.13 Diode turn-off energy dissipation per pulse

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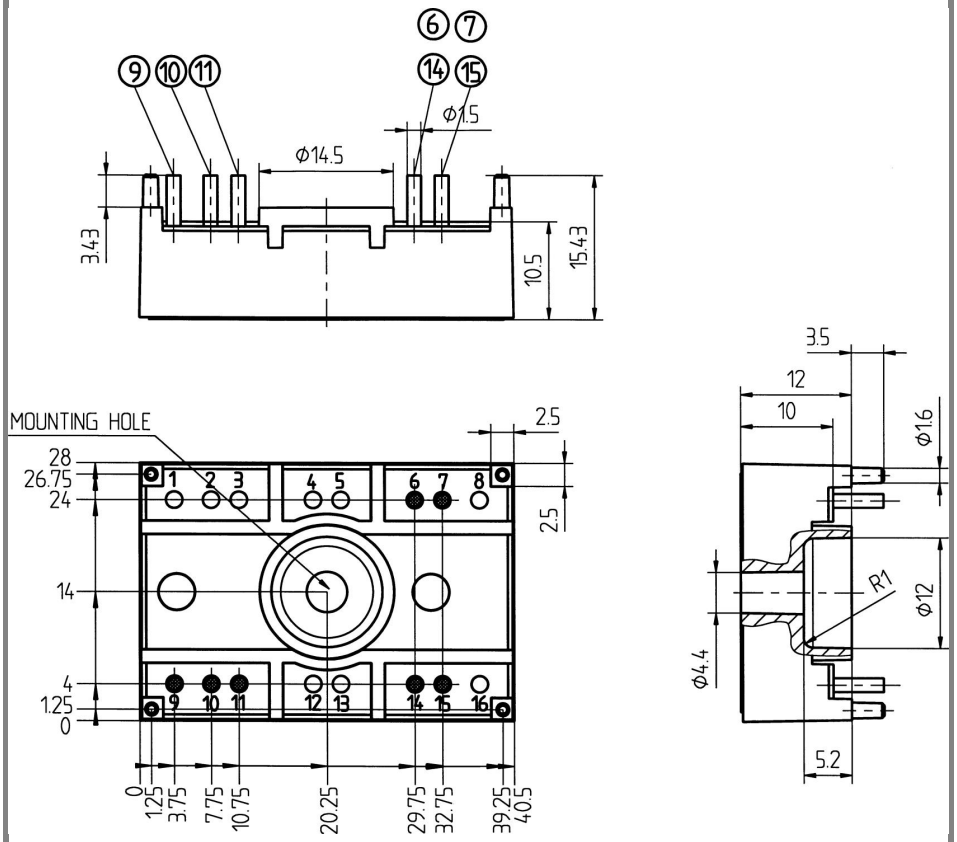
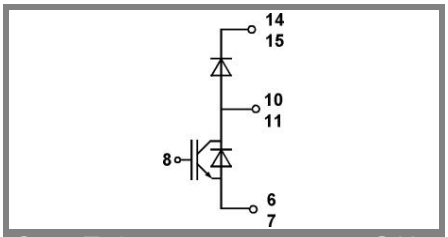
UL Recognized
File no. E 63532

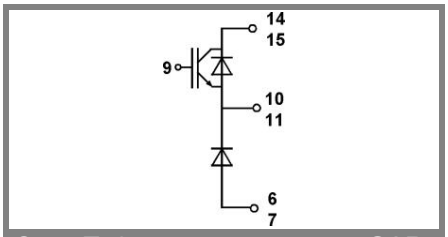
Dimensions in mm



Case T18



Case T18 GAL



Case T18 GAR

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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